





120V DUAL NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN SM-8

Features

- BV_{CEO} > 120V
- I_C = 0.5A High Continuous Current
- High Gain > 400 @ 200mA
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- · Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

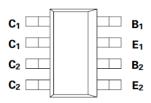
Mechanical Data

- Case: SM-8 (8 LEAD SOT223)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.117 grams (Approximate)

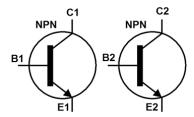
SM-8



Top View



Top View Pin Out



Equivalent Circuit

Ordering Information (Notes 4 and 5)

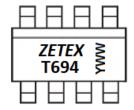
Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZDT694TA	AEC-Q101	T694	7	12	1,000
ZDT694QTA	Automotive	T694	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SM-8



T694 = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 4 = 2014) WW = Week Code 01-52



Absolute Maximum Ratings (@T_A = +25 ℃, unless otherwise specified.)

Characteristic	Symbol	NPN	Unit
Collector-Base Voltage	V _{CBO}	120	V
Collector-Emitter Voltage	V _{CEO}	120	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	0.5	Α
Peak Pulse Current (Note 5)	I _{CM}	1	Α

Thermal Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Collector Power Dissipation	(Note 5)	D	2.25	W	
Collector Fower Dissipation	(Note 6)	P _D	2.75	VV	
Thermal Desigtance Junction to Ambient	(Note 5)	Б	55.6	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	45.5	*C/VV	
Thermal Resistance, Junction to Leads (Note 7)		R _{0JL}	30.7	°C/W	
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	Ç		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

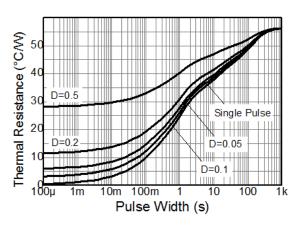
- 5. For a device with any single die active and mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.6. Same as Note 5, except both die are active and equally sharing power.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

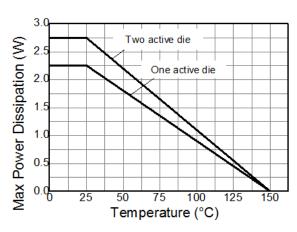
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.





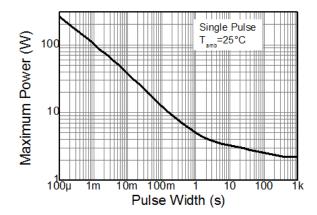
Thermal Characteristics and Derating Information





Transient Thermal Impedance

Derating Curve



Pulse Power Dissipation





Electrical Characteristics (@TA = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_CBO	120	_	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV_CEO	120	_	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	_	_	V	$I_E = 100 \mu A$
Collector Cutoff Current	I _{CBO}	_	_	0.1	μΑ	V _{CB} = 100V
Emitter Cutoff Current	I _{EBO}	_	_	0.1	μΑ	V _{EB} = 5.6V
		500	_	_	-	$I_C = 150 \text{mA}, V_{CE} = 2V$
DC current transfer Static ratio (Note 8)	h _{FE}	400	_	_		$I_C = 200 \text{mA}, V_{CE} = 2V$
		150	_	_		$I_C = 400 mA$, $V_{CE} = 2V$
Collector-Emitter Saturation Voltage (Note 9)	V	_	_	0.25	V	$I_C = 0.1A$, $I_B = 0.5mA$
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	_	_	0.50		$I_C = 0.4A, I_B = 5mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	_	_	0.9	V	$I_C = 1A, I_B = 10mA$
Base-Emitter Turn-on Voltage (Note 9)	$V_{BE(on)}$	_		0.9	V	$I_C = 1A$, $V_{CE} = 2V$
Transitional Frequency	f _T	130			MHz	$I_C = 50$ mA, $V_{CE} = 5$ V, $f = 50$ MHz
Input Capacitance	C _{ibo}	_	200	_	pF	$V_{EB} = 0.5V$, $f = 1MHz$,
Output Capacitance	C _{obo}	_	9	_	pF	V _{EB} = 10V, f = 1MHz,
Switching Time	t _{on}		80		ns	V _{CC} = 50V, I _C = 100mA,
Switching Time	t _{off}		2900		ns	$I_{B1} = -I_{B2} = 10mA$

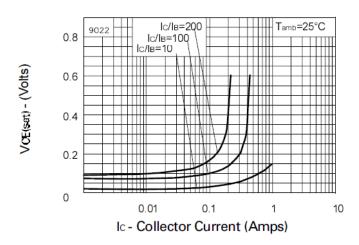
Note:

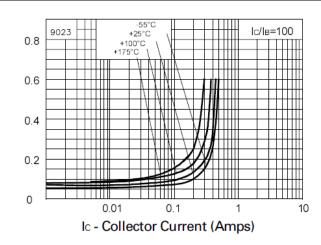
9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25 ℃, unless otherwise specified.)

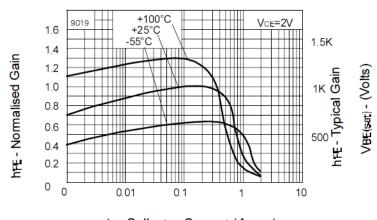
VCE(sat) - (Volts)

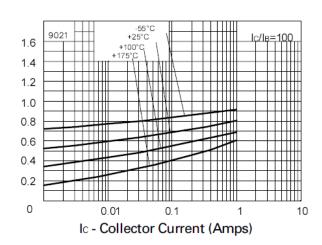




VCE(sat) v IC

VCE(sat) v IC

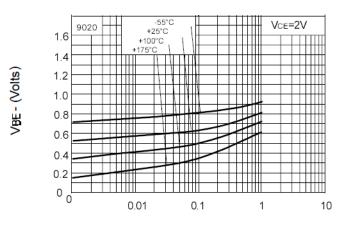




Ic - Collector Current (Amps)

VBE(sat) v IC

hFE v IC



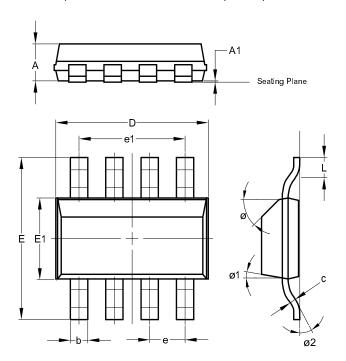
Ic - Collector Current (Amps)

VBE(on) v IC



Package Outline Dimensions

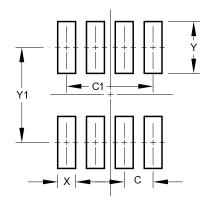
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SM-8					
Dim	Min	Max	Тур		
Α		1.70	1.60		
A 1	0.02	0.10	0.04		
b	0.70	0.90	0.80		
C	0.24	0.32	0.28		
D	6.30	6.70	6.60		
е	1.53 REF				
e1	4.59 REF				
Е	6.70	7.30	7.00		
E1	3.30	3.70	3.50		
L	0.75	1.00	0.90		
Ø			45°		
Ø1		15°			
Ø2			10°		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	1.52		
C1	4.6		
Х	0.95		
Υ	2.80		
Y1	6.80		





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